

# PMEG2005AEL

0.5 A ultra low  $V_F$  MEGA Schottky barrier rectifier in leadless ultra small SOD882 package

Rev. 02 — 27 April 2004

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection encapsulated in a SOD882 leadless ultra small plastic package.

### 1.2 Features

Forward current: 0.5 AReverse voltage: 20 VUltra low forward voltage

- Leadless ultra small plastic package
- Power dissipation comparable to SOT23.

### 1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low voltage rectification
- High efficiency DC-to-DC conversion
- Low power consumption applications.

#### 1.4 Quick reference data

Table 1: Quick reference data

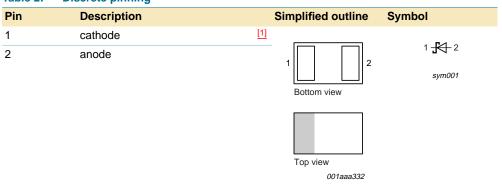
Symbol	Parameter	Value	Unit
I <sub>F</sub>	forward current	0.5	Α
V <sub>R</sub>	reverse voltage	20	V





# 2. Pinning information

Table 2: Discrete pinning



<sup>[1]</sup> The marking bar indicates the cathode.

### 3. Ordering information

Table 3: Ordering information

Type number	Package			
	Name	Description	Version	
PMEG2005AEL	-	leadless ultra small plastic package; 2 terminals; body 1.0 $\times$ 0.6 $\times$ 0.5 mm	SOD882	

## 4. Marking

Table 4: Marking

Type number	Marking code
PMEG2005AEL	F2

## 5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	continuous reverse voltage		-	20	V
I <sub>F</sub>	continuous forward current		-	0.5	Α
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	2.5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8 ms square wave	-	3	Α
$T_j$	junction temperature		<u>[1]</u> -	150	°C
$T_{amb}$	operating ambient temperature		<u>[1]</u> –65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

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[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses. Nomograms for determining the reverse power losses P<sub>R</sub> and I<sub>F(AV)</sub> rating will be available on request.

### 6. Thermal characteristics

#### Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2] 500	K/W

<sup>[1]</sup> Refer to SOD882 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.

#### 7. Characteristics

Table 7: Characteristics

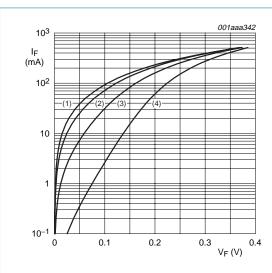
 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified

Symbol	Parameter	Conditions		Тур	Max	Unit
V <sub>F</sub>	continuous forward voltage	see Figure 1;				
		$I_F = 0.1 \text{ mA}$		25	60	mV
		I <sub>F</sub> = 1 mA		75	110	mV
		I <sub>F</sub> = 10 mA		135	190	mV
		I <sub>F</sub> = 100 mA		220	290	mV
		I <sub>F</sub> = 500 mA		375	440	mV
I <sub>R</sub>	continuous reverse current	see Figure 2;	[1]			
		V <sub>R</sub> = 10 V		210	600	μΑ
		$V_R = 20 V$		370	1500	μΑ
$C_d$	diode capacitance	$V_R = 1 V$ ; $f = 1 MHz$ ; see Figure 3		19	25	pF

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

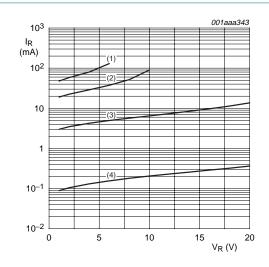
<sup>[2]</sup> For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses. Nomograms for determining the reverse power losses P<sub>R</sub> and I<sub>F(AV)</sub> rating will be available on request.





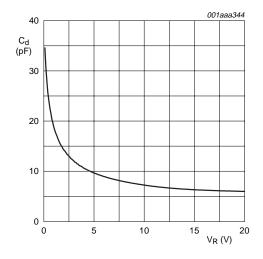
- (1)  $T_i = 150 \,^{\circ}\text{C}$ .
- (2)  $T_i = 125 \, ^{\circ}C$ .
- (3)  $T_j = 85 \,^{\circ}\text{C}$ .
- (4)  $T_j = 25 \, ^{\circ}C$ .

Fig 1. Forward current as a function of forward voltage; typical values.



- (1)  $T_i = 150 \,^{\circ}\text{C}$ .
- (2)  $T_i = 125 \,^{\circ}\text{C}$ .
- (3)  $T_j = 85 \, ^{\circ}\text{C}$ .
- (4)  $T_j = 25 \, ^{\circ}C$ .

Fig 2. Reverse current as a function of reverse voltage; typical values.



 $T_{amb} = 25 \, ^{\circ}C$ ; f = 1 MHz.

Fig 3. Diode capacitance as a function of reverse voltage; typical values.



## 8. Package outline

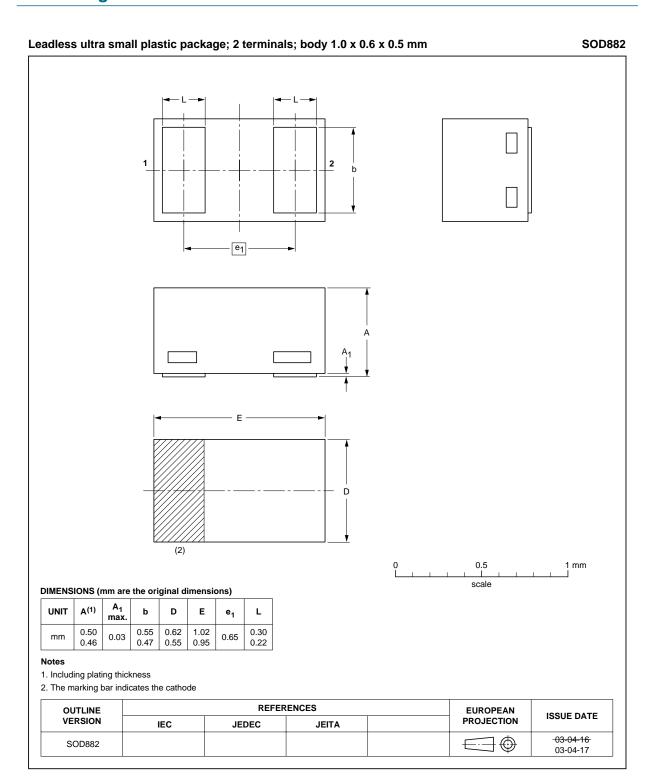


Fig 4. Package outline.

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# 9. Revision history

#### Table 8: Revision history

Document ID	Release date	Data sheet status	Change notice	Order number	Supersedes
PMEG2005AEL_2	20040427	Product data	-	9397 750 13201	PMEG2005AEL_1
Modifications: • General description changed.					
PMEG2005AEL_1	20040419	Product data	-	9397 750 12465	-



#### 10. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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# PMEG2005AEL



0.5 A ultra low V<sub>F</sub> MEGA Schottky rectifier

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Date of release: 27 April 2004 Document order number: 9397 750 13201

Published in The Netherlands

